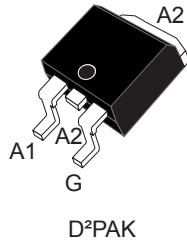
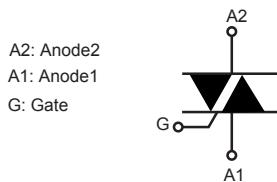


## 8 A - 800 V logic level T-series Triac in D<sup>2</sup>PAK



### Features

- 150 °C maximum junction temperature
- Three quadrants
- High commutation on resistive loads
- Surge capability  $V_{DSM}$ ,  $V_{RSM} = 900$  V
- Benefits:
  - Easy direct control by MCU thanks to low 10 mA  $I_{GT}$
  - Increase of thermal margin due to extended working  $T_j$  up to 150 °C



### Applications

- General purpose AC line load switching
- Small home appliances with resistive loads
- Hybrid relays
- Inrush current limiting circuits
- Overvoltage crowbar protection



### Description

The SMD T810T-8G Triac can be used for the on/off or phase angle control function in general purpose AC switching with resistive loads. A Logic level T-series Triac, the T810T-8G can be controlled directly from an MCU with a simplified circuit.

T-series triacs are optimized for high EMI constraints. The surface mount D<sup>2</sup>PAK package enables compact SMT designs for automated manufacturing.

D<sup>2</sup>PAK's molding compound resin is halogen-free and meets UL94 flammability standard level V0.

Package environmentally friendly ECOPACK<sup>2</sup> graded (RoHS and Halogen Free compliance).

Product status link	
T810T-8G	
Product summary	
I <sub>T(RMS)</sub>	8 A
V <sub>DRM/V<sub>RRM</sub></sub>	800 V
V <sub>DSM/V<sub>RSM</sub></sub>	900 V
I <sub>GT</sub>	10 mA

## 1 Characteristics

**Table 1. Absolute maximum ratings (limiting values),  $T_j = 25^\circ\text{C}$  unless otherwise specified**

Symbol	Parameter		Value	Unit
$I_{T(\text{RMS})}$	RMS on-state current (full sine wave)	$T_c = 131^\circ\text{C}$	8	A
$I_{TSM}$	Non repetitive surge peak on-state current ( $T_j$ initial = $25^\circ\text{C}$ )	$t = 16.7 \text{ ms}$	63	A
		$t = 20 \text{ ms}$	60	
$I^2t$	$I^2t$ value for fusing	$t_p = 10 \text{ ms}$	$T_j = 25^\circ\text{C}$	$24 \text{ A}^2\text{s}$
$dI/dt$	Critical rate of rise of on-state current, $I_G = 2 \times I_{GT}$ , $t_r \leq 100 \text{ ns}$	$f = 50 \text{ Hz}$	$T_j = 25^\circ\text{C}$	$100 \text{ A}/\mu\text{s}$
$V_{DRM}/V_{RRM}$	Repetitive peak off-state voltage	$T_j = 125^\circ\text{C}$	800	V
		$T_j = 150^\circ\text{C}$	600	V
$V_{DSM}/V_{RSM}$	Non Repetitive peak off-state voltage	$t_p = 10 \text{ ms}$	$T_j = 25^\circ\text{C}$	900 V
$I_{GM}$	Peak gate current	$T_j = 150^\circ\text{C}$	4	A
		$t_p = 20 \mu\text{s}$	$T_j = 150^\circ\text{C}$	5 V
$P_{G(AV)}$	Average gate power dissipation	$T_j = 150^\circ\text{C}$	1	W
$T_{stg}$	Storage junction temperature range		-40 to +150	$^\circ\text{C}$
$T_j$	Operating junction temperature range		-40 to +150	$^\circ\text{C}$

**Table 2. Electrical characteristics ( $T_j = 25^\circ\text{C}$ , unless otherwise specified)**

Symbol	Test conditions	Quadrants; $T_j$		Value	Unit
$I_{GT}^{(1)}$	$V_D = 12 \text{ V}$ , $R_L = 30 \Omega$	I - II - III	Min.	0.5	mA
		I - II - III	Max.	10	
$V_{GT}$	$V_D = 12 \text{ V}$ , $R_L = 30 \Omega$	I - II - III	Max.	1.3	V
$V_{GD}$	$V_D = 800 \text{ V}$ , $R_L = 3.3 \text{ k}\Omega$	$T_j = 125^\circ\text{C}$	I - II - III	Min.	0.2 V
$I_L$	$I_G = 1.2 \times I_{GT}$	I - III	Max.	20	mA
	$I_G = 1.2 \times I_{GT}$	II	Max.	25	mA
$I_H^{(2)}$	$I_T = 500 \text{ mA}$ , gate open		Max.	15	mA
$dV/dt^{(2)}$	$V_D = 536 \text{ V}$ , gate open	$T_j = 125^\circ\text{C}$	Min.	250	$\text{V}/\mu\text{s}$
	$V_D = 402 \text{ V}$ , gate open	$T_j = 150^\circ\text{C}$	Min.	170	$\text{V}/\mu\text{s}$
$(dI/dt)c^{(2)}$	$(dV/dt)c = 0.1 \text{ V}/\mu\text{s}$	$T_j = 125^\circ\text{C}$	Min.	6	A/ms
		$T_j = 150^\circ\text{C}$	Min.	4.2	
	$(dV/dt)c = 10 \text{ V}/\mu\text{s}$	$T_j = 125^\circ\text{C}$	Min.	3.2	A/ms
		$T_j = 150^\circ\text{C}$	Min.	1.4	

1. Minimum  $I_{GT}$  is guaranteed at 5% of  $I_{GT}$  max

2. For both polarities of A2 referenced to A1.

**Table 3. Static characteristics**

Symbol	Test conditions	T <sub>j</sub>		Value	Unit
V <sub>TM</sub> <sup>(1)</sup>	I <sub>T</sub> = 11.3 A, t <sub>p</sub> = 380 µs	25 °C	Max.	1.55	V
V <sub>TO</sub> <sup>(1)</sup>	Threshold on-state voltage	150 °C	Max.	0.85	V
R <sub>D</sub> <sup>(1)</sup>	Dynamic resistance	150 °C	Max.	57	mΩ
I <sub>DRM</sub> /I <sub>RRM</sub>	V <sub>DRM</sub> = V <sub>RRM</sub> = 800 V	25 °C	Max.	5	µA
		125°C		0.8	mA
	V <sub>DRM</sub> = V <sub>RRM</sub> = 600 V	150 °C	Max.	2.4	mA

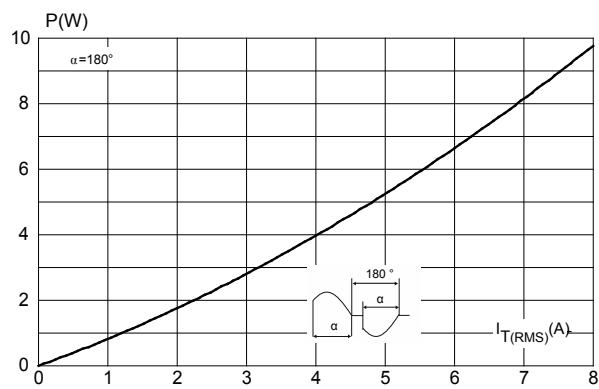
1. For both polarities of A2 referenced to A1.

**Table 4. Thermal resistance**

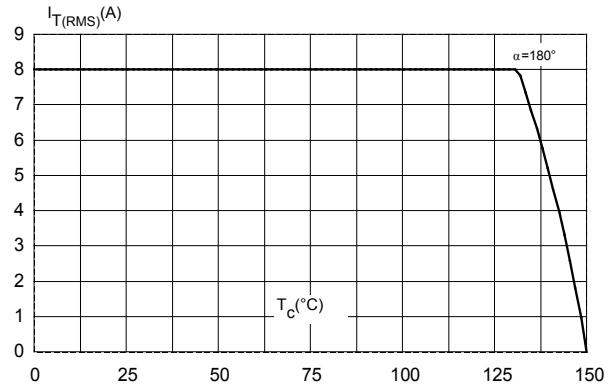
Symbol	Parameter	Value	Unit
R <sub>th(j-c)</sub>	Junction to case (AC)	Max.	°C/W
R <sub>th(j-a)</sub>	Junction to ambient (AC) for S <sub>Cu</sub> = 2 cm <sup>2</sup>	Typ.	

## 1.1 Characteristics (curves)

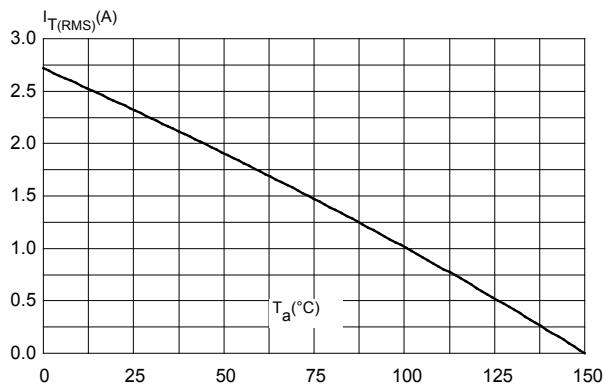
**Figure 1. Maximum power dissipation versus on-state RMS current**



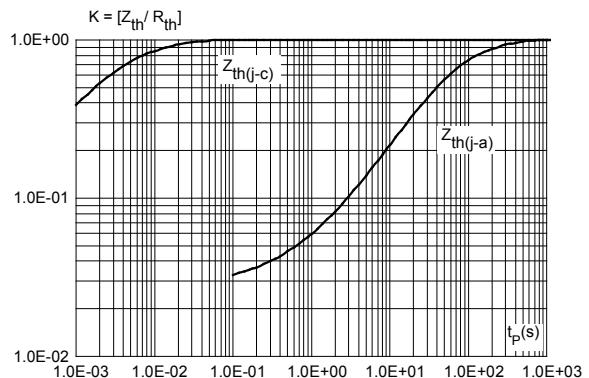
**Figure 2. On-state RMS current versus case temperature**



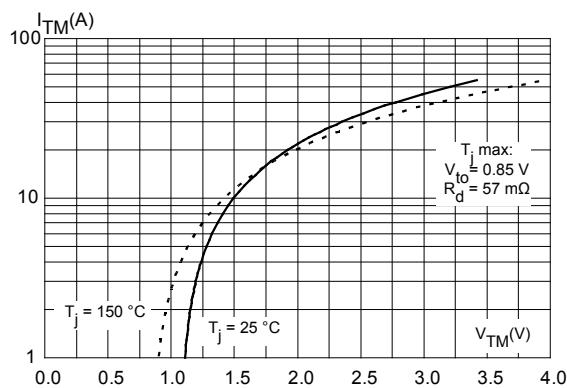
**Figure 3. On-state RMS current versus ambient temperature (free air convection)**



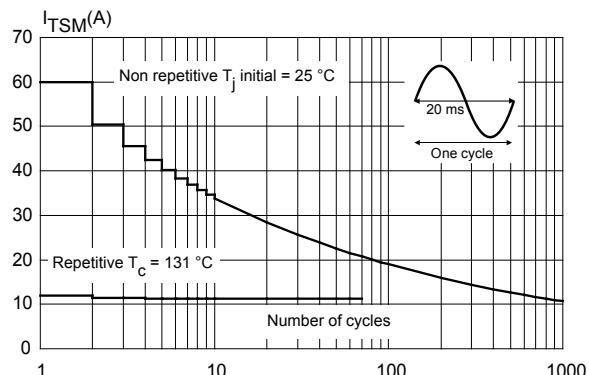
**Figure 4. Relative variation of thermal impedance versus pulse duration**

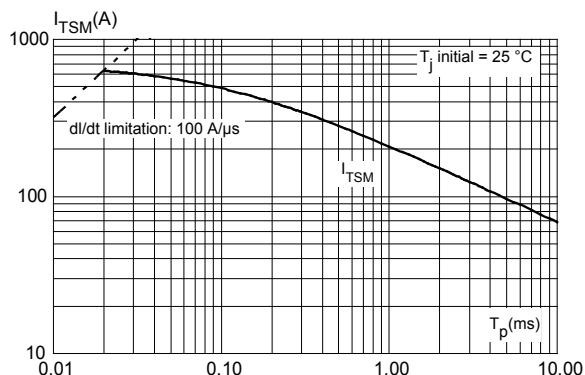
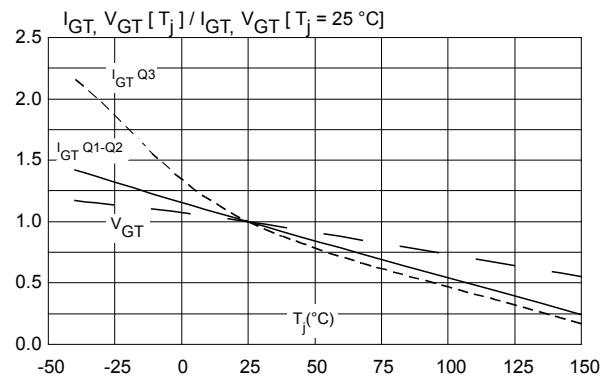
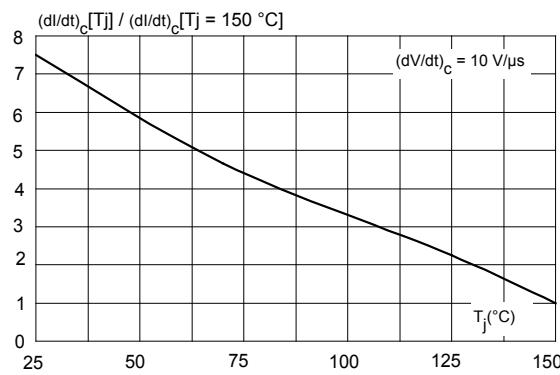
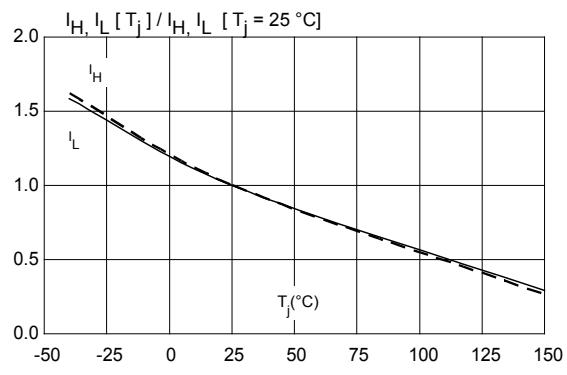
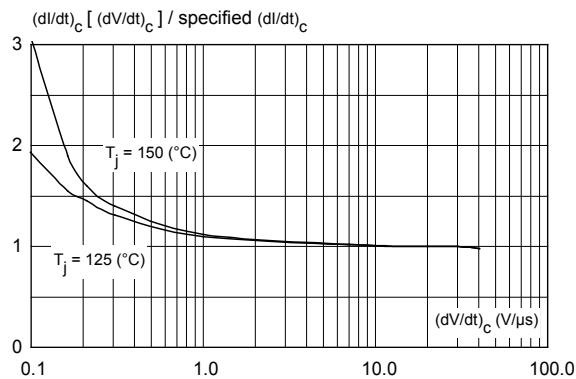
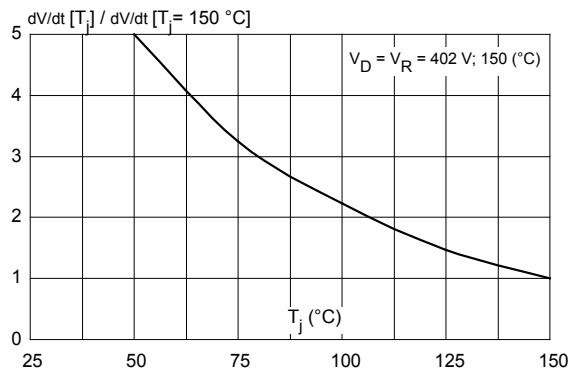


**Figure 5. On-state characteristics (maximum values)**

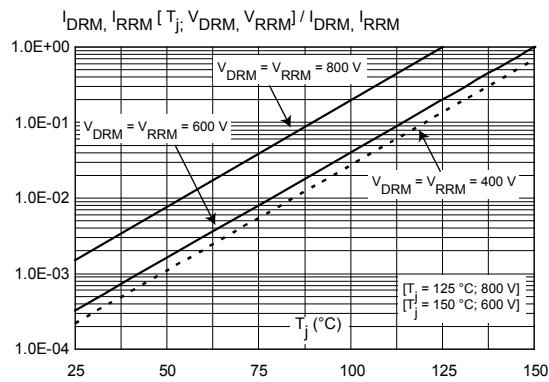


**Figure 6. Surge peak on-state current versus number of cycles**

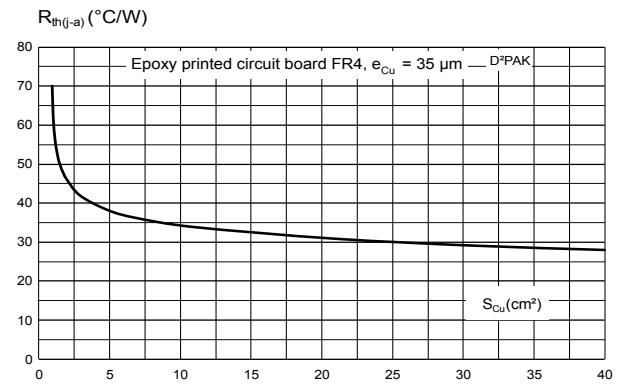


**Figure 7. Non repetitive surge peak on-state current**

**Figure 8. Relative variation of gate trigger current and gate voltage versus junction temperature (typical values)**

**Figure 9. Relative variation of critical rate of decrease of main current versus junction temperature (typical values)**

**Figure 10. Relative variation of holding current and latching current versus junction temperature (typical values)**

**Figure 11. Relative variation of critical rate of decrease of main current (dl/dt)c versus reapplied (dl/dt)c (maximum values)**

**Figure 12. Relative variation of static dV/dt immunity versus junction temperature (typical values)**


**Figure 13. Relative variation of leakage current versus junction temperature for different values of blocking voltage (typical values)**



**Figure 14. Thermal resistance junction to ambient versus copper surface under tab**



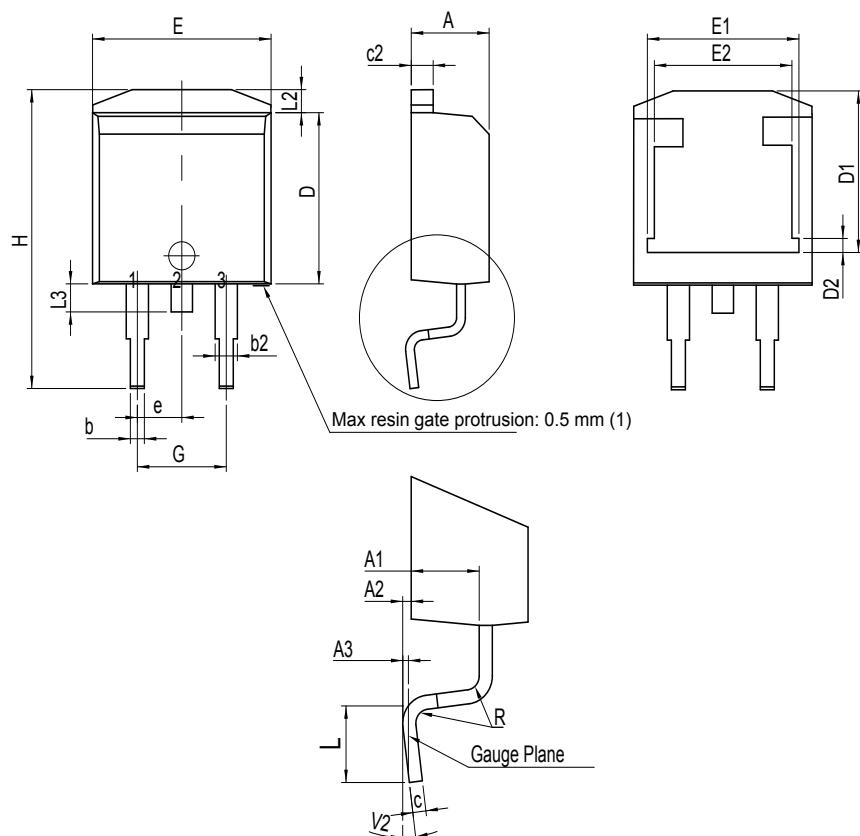
## 2 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 2.1 D<sup>2</sup>PAK package information

- ECOPACK2 compliant
- Lead-free package leads finishing
- Molding compound resin is halogen-free and meets UL standard level V0

Figure 15. D<sup>2</sup>PAK package outline



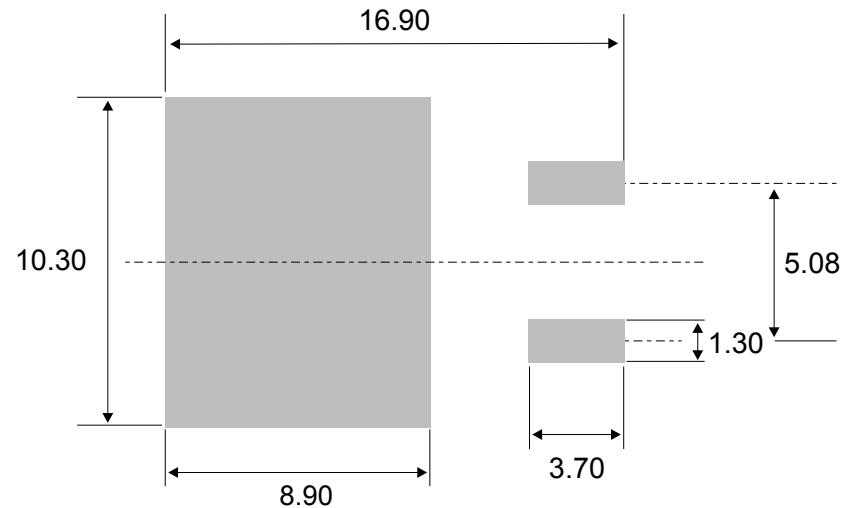
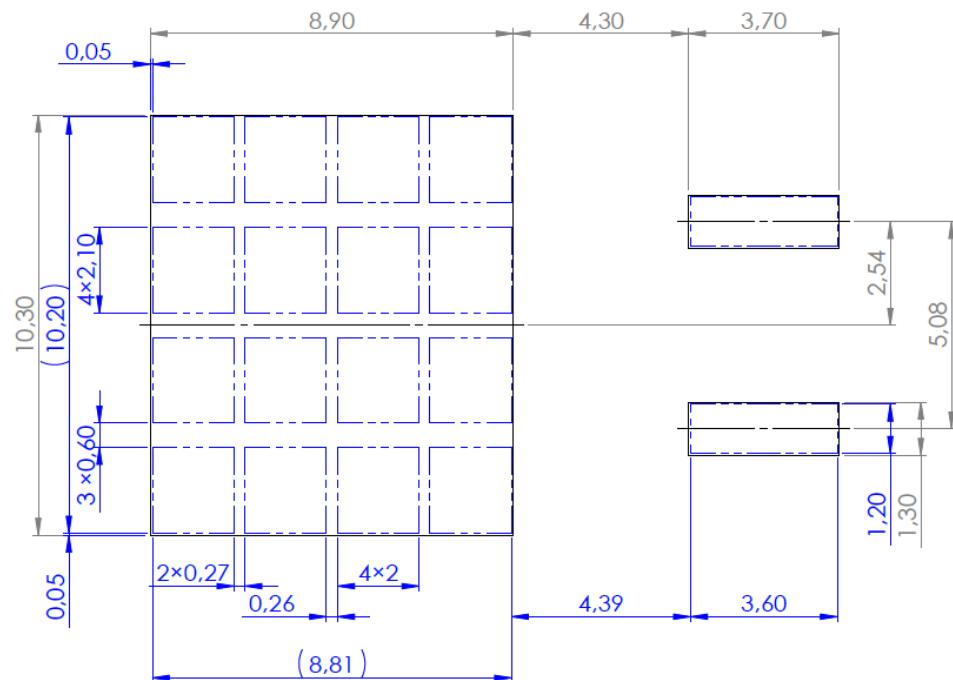
(1) Resin gate is accepted in each of position shown on the drawing, or their symmetrical.

Table 5. D<sup>2</sup>PAK package mechanical data

Ref.	Dimensions					
	Millimeters			Inches <sup>(1)</sup>		
	Min.	Typ.	Max.	Min.	Typ.	Max.
A	4.30		4.60	0.1693		0.1811
A1	2.49		2.69	0.0980		0.1059
A2	0.03		0.23	0.0012		0.0091
A3		0.25			0.0098	
b	0.70		0.93	0.0276		0.0366
b2	1.25		1.7	0.0492		0.0669
c	0.45		0.60	0.0177		0.0236
c2	1.21		1.36	0.0476		0.0535
D	8.95		9.35	0.3524		0.3681
D1	7.50		8.00	0.2953		0.3150
D2	1.30		1.70	0.0512		0.0669
e		2.54			0.1	
E	10.00		10.28	0.3937		0.4047
E1	8.30		8.70	0.3268		0.3425
E2	6.85		7.25	0.2697		0.2854
G	4.88		5.28	0.1921		0.2079
H	15		15.85	0.5906		0.6240
L	1.78		2.28	0.0701		0.0898
L2	1.19		1.40	0.0468		0.0551
L3	1.40		1.75	0.0551		0.0689
R		0.40			0.0157	
V2 <sup>(2)</sup>	0°		8°	0°		8°

1. Dimensions in inches are given for reference only

2. Degrees

Figure 16. D<sup>2</sup>PAK recommended footprint (dimensions are in mm)Figure 17. D<sup>2</sup>PAK stencil definitions(dimensions are in mm)

### 3 Ordering information

Figure 18. Ordering information scheme

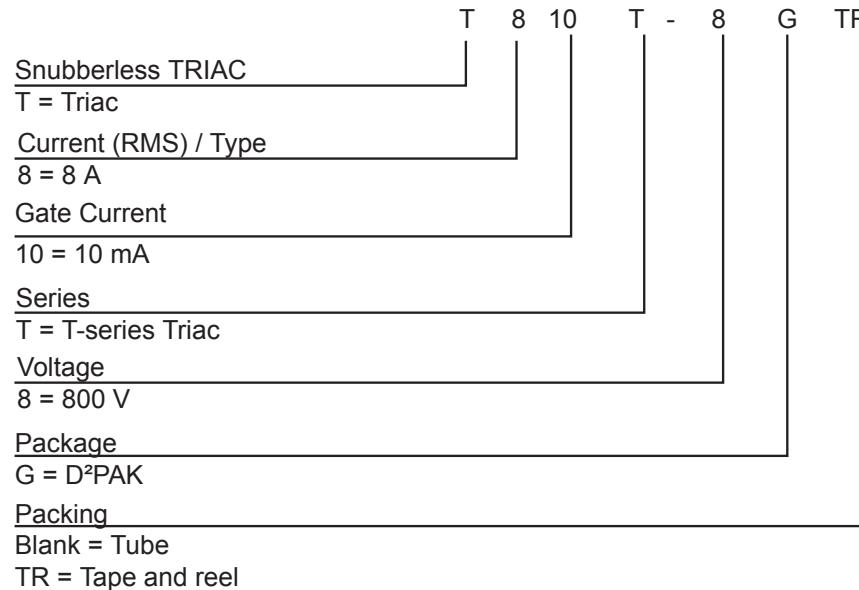


Table 6. Ordering information

Order code	Marking	Package	Weight	Base qty.	Delivery mode
T810T-8G-TR	T810T-8G	D <sup>2</sup> PAK	1.6 g	1000	Tape and reel
T810T-8G				50	Tube

## Revision history

**Table 7. Document revision history**

Date	Version	Changes
04-Jun-2020	1	Initial release.
20-Oct-2020	2	Updated <a href="#">Table 5</a> .

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